

FIG 1

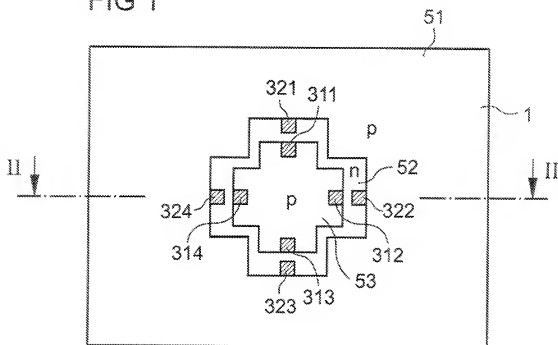


FIG 2

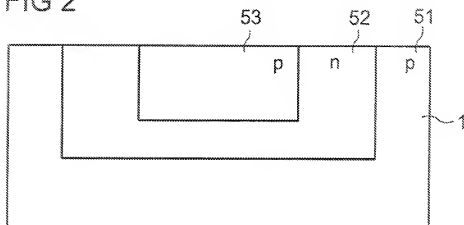
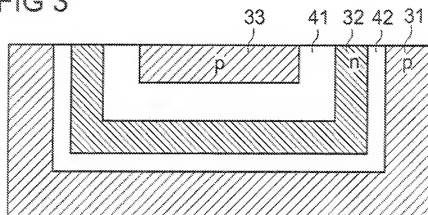


FIG 3



A detailed cross-sectional diagram of a semiconductor device, labeled FIG 4. The device consists of several layers and regions. At the base is a substrate labeled '1' with a hatched pattern. Above it is a layer labeled '2'. Within layer 2 are two rectangular regions: a larger one labeled 'n' and a smaller one nested inside labeled 'p'. Above the 'n' region is another layer labeled '31'. On top of layer 31 are two vertical structures. The left one has a downward arrow labeled 'IK' and an upward arrow labeled 'IS', with labels 324 and 41 pointing to its sides. The right one has a downward arrow labeled 'IK' and an upward arrow labeled 'IS', with labels 322 and 32 pointing to its sides. Between these two structures is a central region labeled '33'. To the left of 33 is a region labeled '314'. Below the 'n' region is a layer labeled 'p'. Dimensions are indicated by double-headed arrows: 'd1' between the bottom of the 'n' region and the top of the 'p' region; 'd2' between the bottom of the 'p' region and the bottom of the substrate; and 'D' between the top surface of the device and the top of the 'n' region. A vertical axis labeled 'B' passes through the center of the device.

[illegible]